# 2.5V Drive Nch MOS FET

## RTR020N05

#### ●Structure

Silicon N-channel MOS FET

## ● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT3).
- 3) Low voltage drive (2.5V drive).

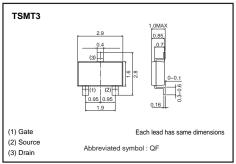
## Applications

Switching

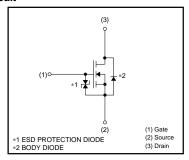
## ●Packaging specifications and hFE

	Package	Taping
Type	Code	TL
	Basic ordering unit (pieces)	3000
RTR020N0	0	

## ●External dimensions (Unit : mm)



#### •Inner circuit



## ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage		V <sub>DSS</sub>	45	V
Gate-source voltage	Vgss	12	V	
Drain current	Continuous	I <sub>D</sub>	±2.0	Α
Drain current	Pulsed	I <sub>DP</sub> *1	±8	Α
Source current	Continuous	Is	0.8	Α
(Body diode)	Pulsed	I <sub>SP</sub> *1	8	А
Total power dissipation	Pp *2	1.0	W	
Channel temperature	Tch	150	°C	
Range of storage temperature	Tstg	-55 to +150	°C	

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

## \*2 Mounted on a ceramic board

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W

<sup>\*</sup> Mounted on a ceramic board

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	10	μΑ	V <sub>GS</sub> =12V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	45	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	Vps= 45V, Vgs=0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5	-	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
0		_	130	180	mΩ	I <sub>D</sub> = 2.0A, V <sub>GS</sub> = 4.5V
Static drain-source on-state resistance	RDS (on)*	_	135	190	mΩ	ID= 2.0A, VGS= 4V
		-	180	250	mΩ	I <sub>D</sub> = 2.0A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub> *	1.5	-	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.0A
Input capacitance	Ciss	_	200	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	45	_	pF	V <sub>G</sub> s=0V
Reverse transfer capacitance	Crss	-	25	-	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	11	-	ns	Vpp≒ 25V
Rise time	tr *	-	16	_	ns	ID= 1.0A
Turn-off delay time	t <sub>d (off)</sub> *	-	21	_	ns	Vgs= 4.5V RL=25Ω
Fall time	t <sub>f</sub> *	-	11	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	2.9	4.1	nC	V <sub>DD</sub> ≒25V V <sub>GS</sub> =4.5V
Gate-source charge	Q <sub>gs</sub> *	-	0.7	-	nC	I <sub>D</sub> = 2.0A
Gate-drain charge	Q <sub>gd</sub> *	_	0.9	_	nC	RL=12.5Ω R <sub>G</sub> =10Ω

<sup>\*</sup>Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

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Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	_	1.2	V	Is= 0.8A. V <sub>GS</sub> =0V

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